

Appl. No. 10/709,651  
Amdt. dated July 12, 2005  
Reply to Office action of March 18, 2005

**Amendments to the Specification:**

Please replace paragraph [0022] with the following amended paragraph:

[0022] Referring to Fig.3, which is a schematic diagram of the aperture plate 18a of Quasar 90. The aperture plate 18a comprises four aperture patterns 18b thereon, which have the shape of a sector and are arranged in the periphery area of the aperture plate 18a. A center point 18c is defined on the aperture plate 18a. A horizontal axis X and a vertical axis Y intersecting the center point 18c are further defined on the aperture plate 18a. The distance between the center point 18c and the aperture pattern 18b is defined by an offset 18d. As shown in Fig.3, the included angle  $\varphi$  of the offset 18d and the horizontal axis X is 90 degrees. Therefore, applying the aperture plate 18a to the scanner system 12 shown in Fig.1 means the lithography system 10 adopts an OAI with Quasar 90 as the light source for exposing photomask. Similarly, if the included angle  $\varphi$  of the offset 18d and the horizontal axis X is 45 degrees, the light source of exposure is a Quasar 45 illumination. Since the present invention focuses on solving the problem of forbidden pitch of dense and semi-dense area occurring under the Quasar 90 illumination, all of the embodiments described below are under the condition of Quasar 90 illumination.